

# Spin Transfer Torque Reversal in Perpendicular Anisotropy Spin Valves

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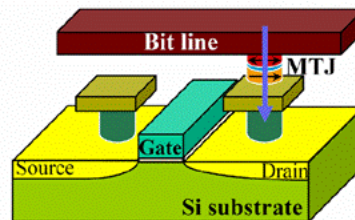
**NSF Award # DMR-1008654**

CMRR Research Review, May 4-5, 2011



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## STT-MRAM

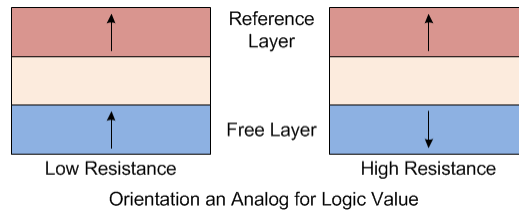


- Spin Valves as Memory Elements
- Promising technology for implementing high-density memory in CMOS logic circuits
  - High Density (compared to SRAM, embedded DRAM)
  - Compatible with CMOS logic process
  - Low Power Consumption (no quiescent power)
- **Replace SRAM, DRAM, Flash**

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## Overview of PMA



- Advantage of PMA materials for STT-MRAM

$$I_{c0} = \left( \frac{2e}{\hbar} \right) \frac{2\alpha}{\eta(\theta)_p} E_B$$

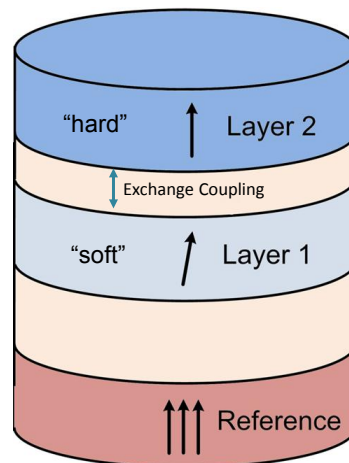
- **Scaling** to small size (reducing V) introduces problems due to increasing  $J_C$ 
  - Also J for driving transistor

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## Summary of Work

- Reduce  $I_C$  for a given  $E_B$  in a device
  - Use bi-layer hard/soft FM coupled structure as free element
- Computational / analytical (simulation based) approach to this problem

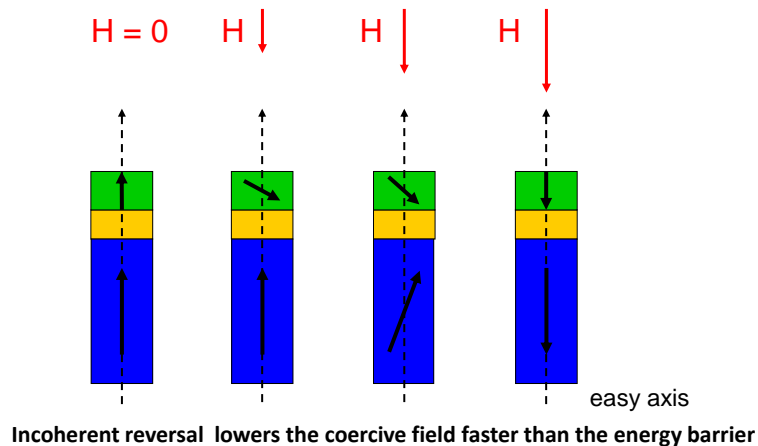


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# Similar, Existing Problem

$H_c$  reduction in switching of magnetic media



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## Approach

1. Development of macrospin simulator program "Spinsim GSL"
  - Public/Free, soon to be published on CMRR site
2. Use program to explore parameter space; find reduction in  $I_C$  (in  $I / J_{\text{exch}}$  parameter space)
3. Compare result with 'reference model', consisting of a single free layer with similar  $E_B$
4. Gain understanding of underlying physics governing the results

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## Macrospin Simulation

- Integration of LLG equation to resolve macrospin behavior

$$\frac{\delta \mathbf{m}}{\delta t} = -\gamma \mathbf{m} \times \mathbf{H}_{eff} - \alpha \mathbf{m} \times \frac{\delta \mathbf{m}}{\delta t} + \frac{\gamma}{\mu_0 M_S} \mathbf{N}$$

Effective field composed of

1. Anisotropy field
2. Self demagnetizing field
3. Mutual dipolar field
4. Effective field due to FM coupling

Spin Transfer Torque term:

$$\mathbf{N}_{st} = \eta(\theta) \frac{\hbar J}{2e d} \mathbf{m} \times [\mathbf{m} \times \mathbf{M}]$$

$\mathbf{M}$  = fixed layer magnetization

$\eta(\theta)$  = STT efficiency [next slide]

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LLG eqn. modified for STT - J.C. Slonczewski MMM 159 (1996); N. Smith cond-mat/0406486  
STT term - Xiao, Zangwill, M.D. Stiles PRB 72,014446 (2005)

## STT Efficiency Functions

- For metallic junctions, using Symmetric Slonczewski Approx<sup>1,2</sup>

$$\eta(\theta) = \frac{q}{A + B \cos(\theta)}$$

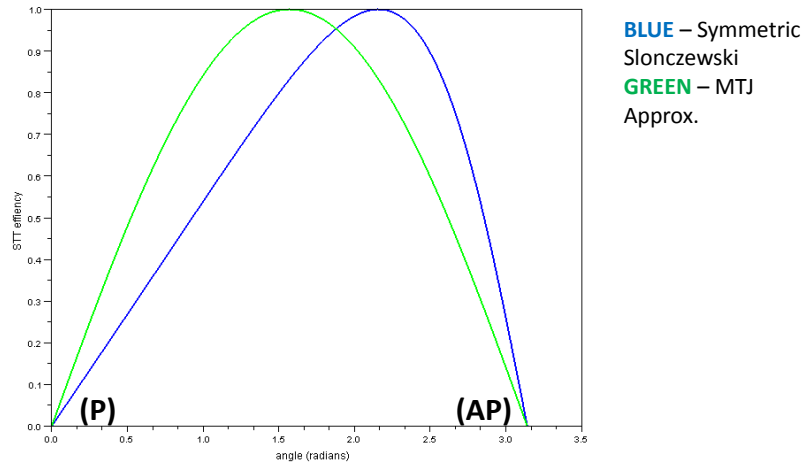
- For tunnel junction, using sin() approximation<sup>3</sup>

$$\eta(\theta) = \eta_0$$

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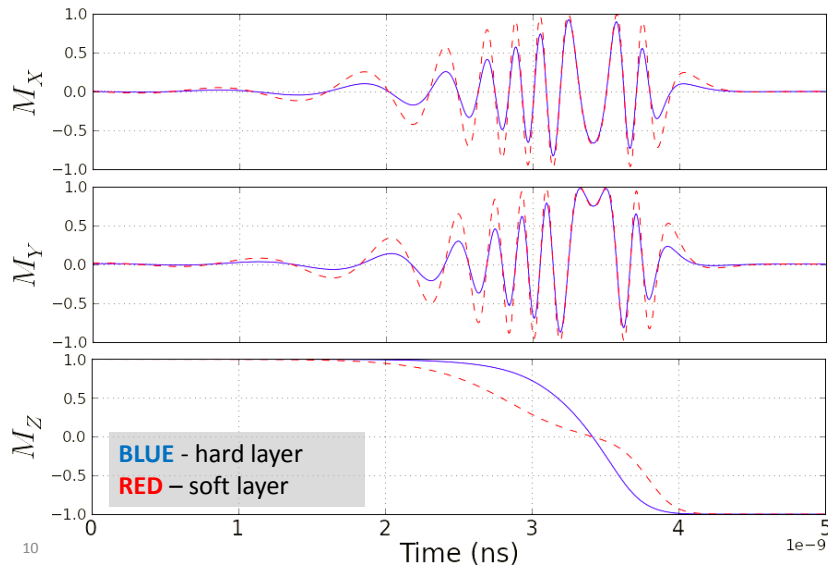
- (1) J.C. Slonczewski MMM 159, L1 (1996)  
(2) J.C. Slonczewski MMM 247, 324 (2002)  
(3) J.C. Slonczewski, J.Z. Sun, MMM 310, 2 (2007)

## STT Efficiency Functions (2)



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## Incoherent Reversal



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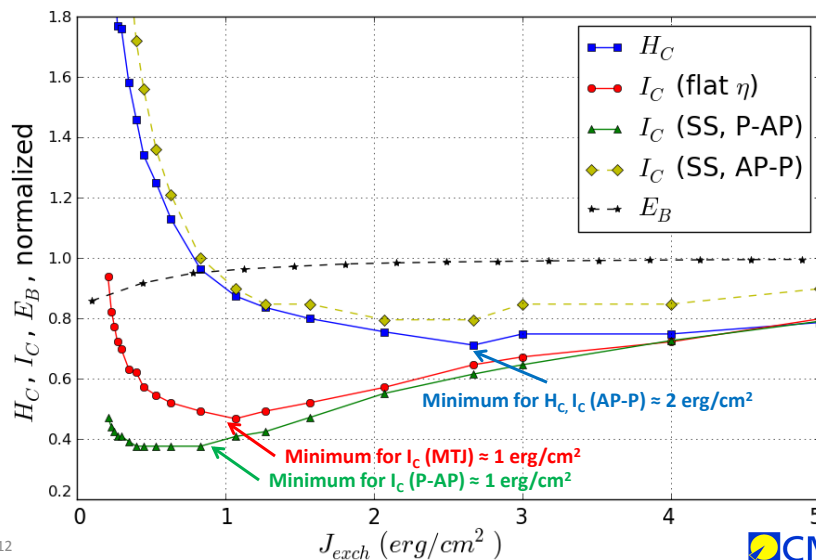
## Results

- **Significant reduction** in  $I_C$  when compared with reference model having similar  $E_B$
- Greater benefit (for worst case) when considering switching at **short timescales**

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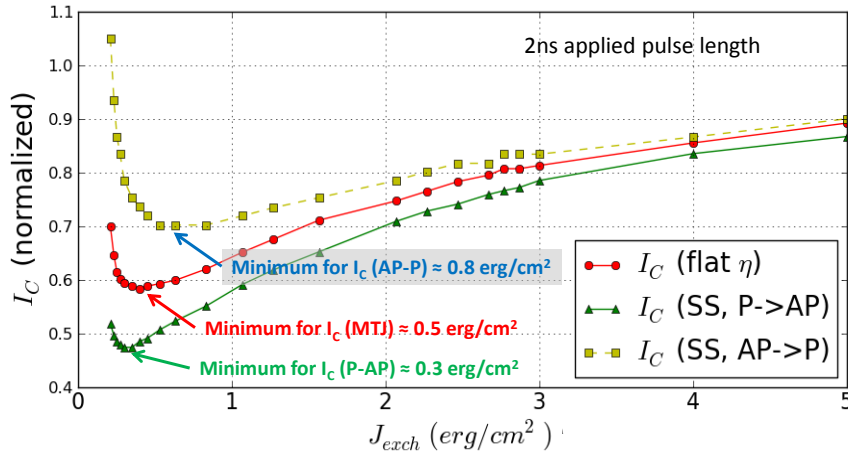
### Effect of Coupling on $I_{C0}$ , $E_B$



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## $I_C$ vs $J_{\text{exch}}$ for Short Time Scales



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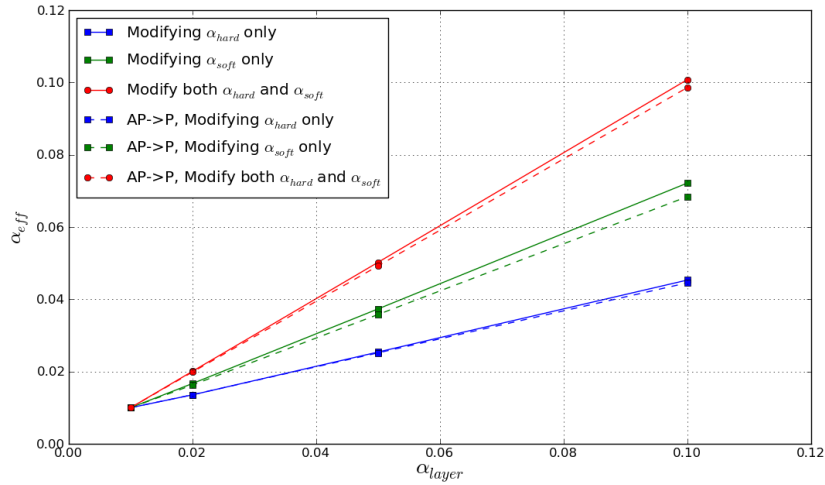


## Another Benefit – Pathway to Reduced Damping

$$I_{C0} = \left( \frac{2e}{\hbar} \right) \frac{2\alpha}{\eta(\theta)p} E_B$$

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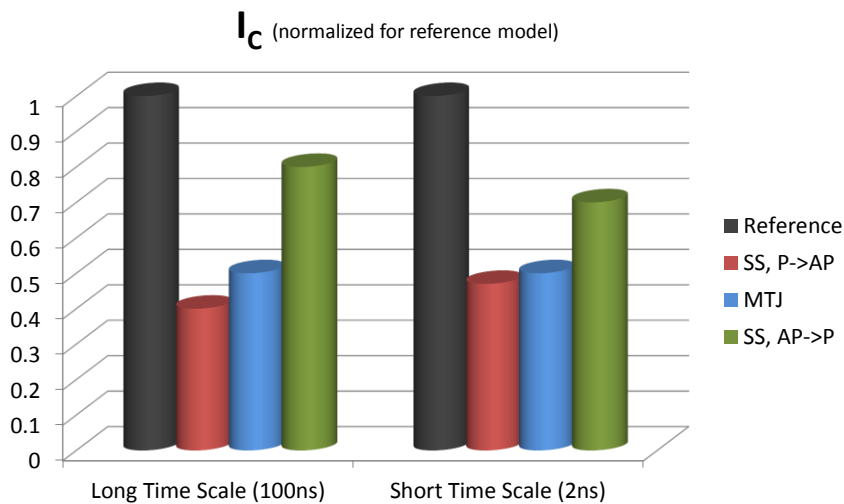
## Computing $\alpha_{\text{eff}}$ for Bi-Layer Structure



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## Summary of Results



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# Acknowledgments

- **Eric Fullerton** & Fullerton Group (UCSD – CMRR)
- **Marko Lubarda**, under V. Lomakin & E. E. Fullerton (UCSD – ECE & CMRR)
  - Energy Barrier Modeling; Co-Author
- **Christel Berthelot** & **Stephane Mangin** (Université Nancy)
  - Macrospin simulator code development
- **Stephanie Moyerman** (UCSD)
  - Mentoring, Spinsim GSL development and research guidance
- **NSF Award # DMR-1008654**

